

BCR16CM-12LB

600V - 16A - Triac



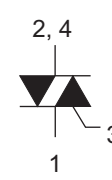
Medium Power Use

R07DS1032EJ0400
 (Previous: REJ03G0457-0300)
 Rev.4.00
 Feb 25, 2013

Features

- $I_{T(RMS)}$: 16 A
- V_{DRM} : 600 V
- I_{FGT} , I_{RGT} , $I_{RGT III}$: 30 mA (20 mA)^{Note6}
- Non-Insulated Type
- Planar Passivation Type

Outline

RENESAS Package code: PRSS0004AG-A (Package name: TO-220AB)	RENESAS Package code: PRSS0004AA-A (Package name: TO-220)
	
	
1. T ₁ Terminal 2. T ₂ Terminal 3. Gate Terminal 4. T ₂ Terminal	

Applications

Contactless AC switch, light dimmer, electronic flasher unit, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, electric fan, solenoid driver, small motor control, copying machine, electric tool, electric heater control, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	16	A	Commercial frequency, sine full wave 360° conduction, T _c = 125°C ^{Note3}
Surge on-state current	I_{TSM}	170	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	I ² t	121	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P _{GM}	5.0	W	
Average gate power dissipation	P _{G(AV)}	0.5	W	
Peak gate voltage	V _{GM}	10	V	
Peak gate current	I _{GM}	2	A	
Junction temperature	T _j	- 40 to +150	°C	
Storage temperature	T _{stg}	- 40 to +150	°C	
Mass	—	2.1	g	Typical value

Electrical Characteristics

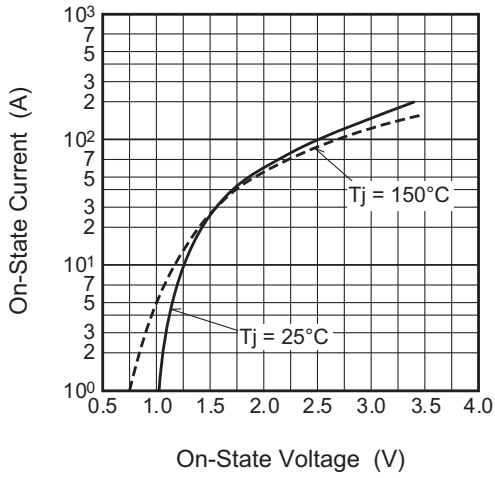
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 150^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.5	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 25\text{ A}$, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	1.5	
	III	V_{RGTIII}	—	—	1.5	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	30^{Note6}	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	30^{Note6}	
	III	I_{RGTIII}	—	—	30^{Note6}	
Gate non-trigger voltage	V_{GD}	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	1.4	$^\circ\text{C}/\text{W}$	Junction to case ^{Note3 Note4}
Critical-rate of rise of off-state commutating voltage ^{Note5}	$(dv/dt)_c$	10/1	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}/150^\circ\text{C}$

- Notes: 1. Gate open.
 2. Measurement using the gate trigger characteristics measurement circuit.
 3. Case temperature is measured at the T_2 tab 1.5 mm away from the molded case.
 4. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $1.0^\circ\text{C}/\text{W}$.
 5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
 6. High sensitivity ($I_{GT} \leq 20\text{ mA}$) is also available. (I_{GT} item: 1)

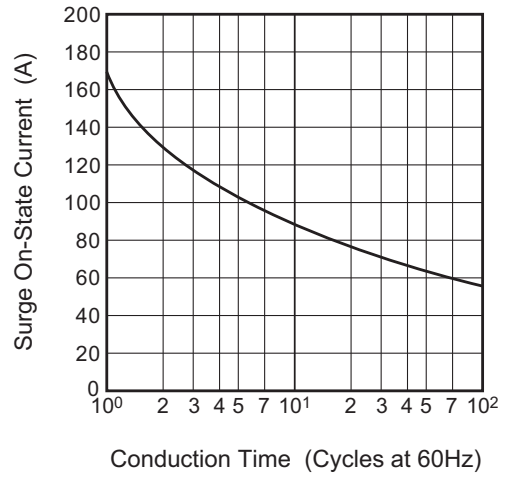
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -8.0\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

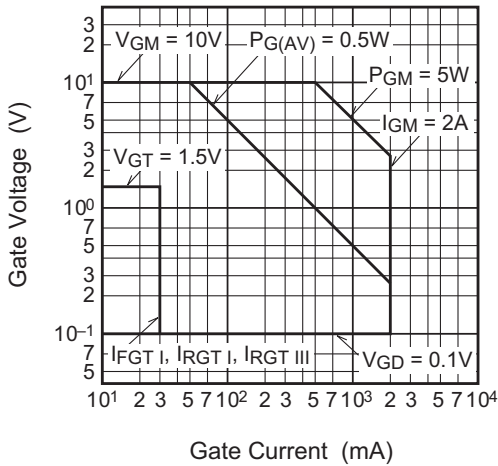
Maximum On-State Characteristics



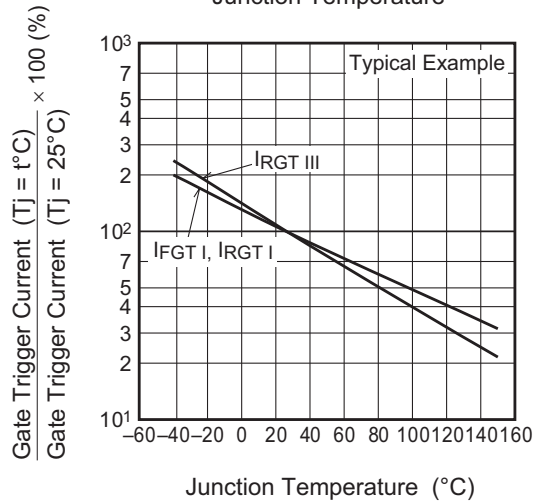
Rated Surge On-State Current



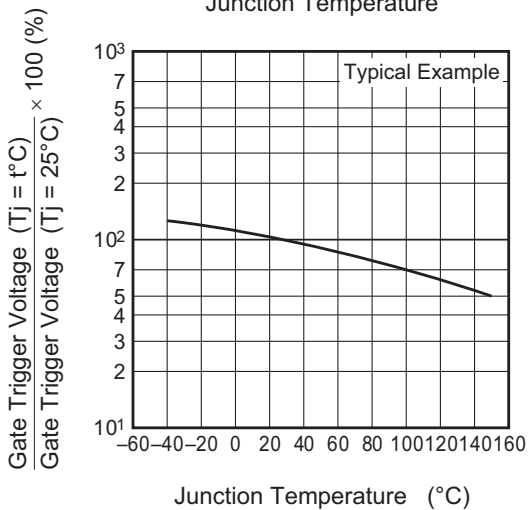
Gate Characteristics (I, II and III)



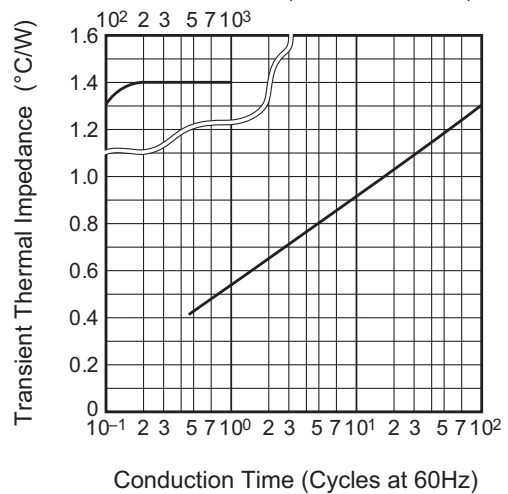
Gate Trigger Current vs. Junction Temperature

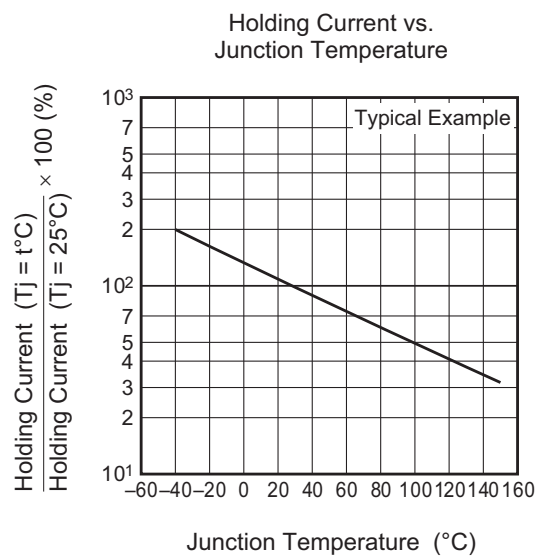
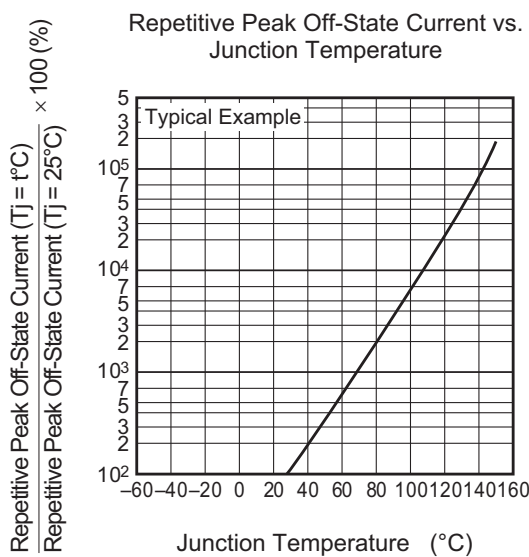
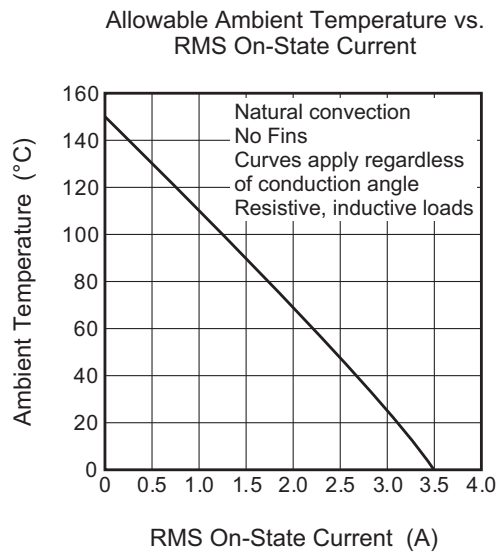
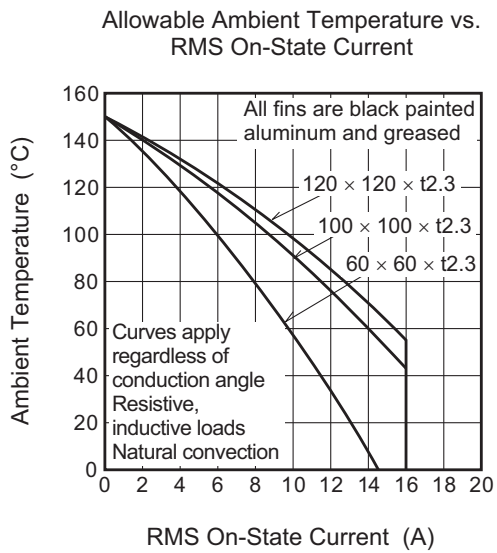
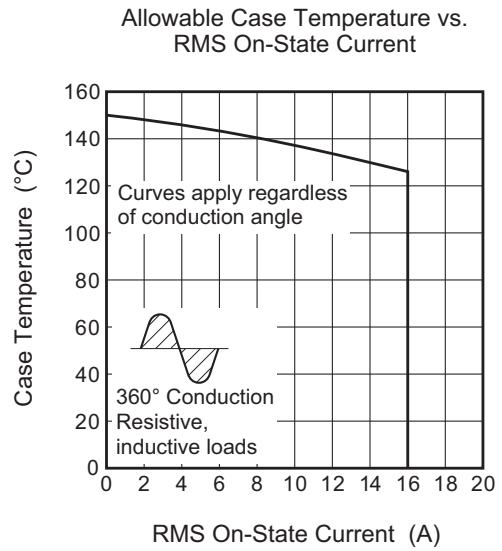
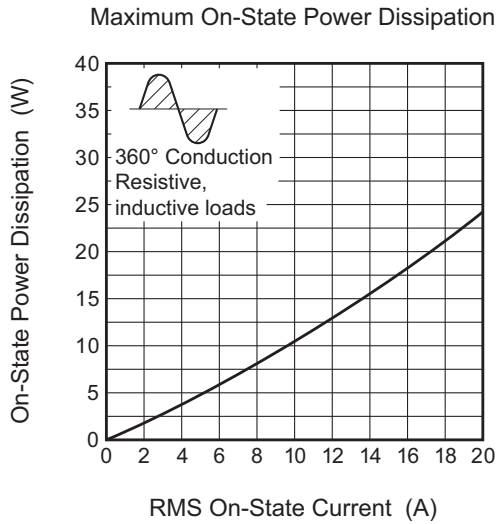


Gate Trigger Voltage vs. Junction Temperature

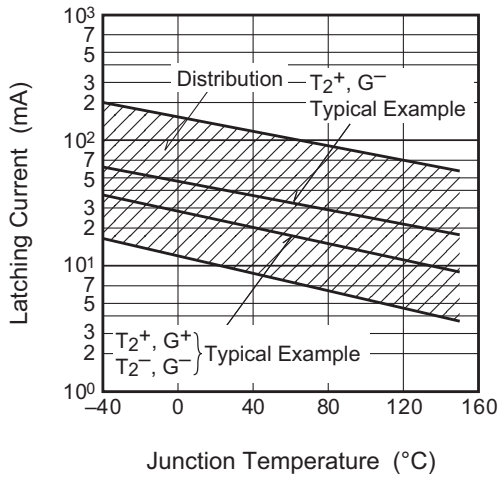


Maximum Transient Thermal Impedance Characteristics (Junction to case)

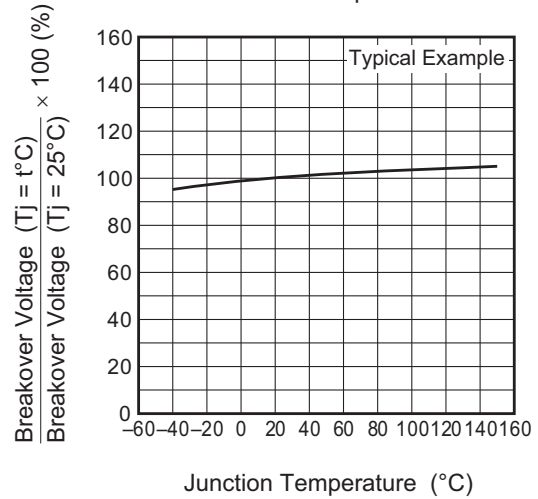




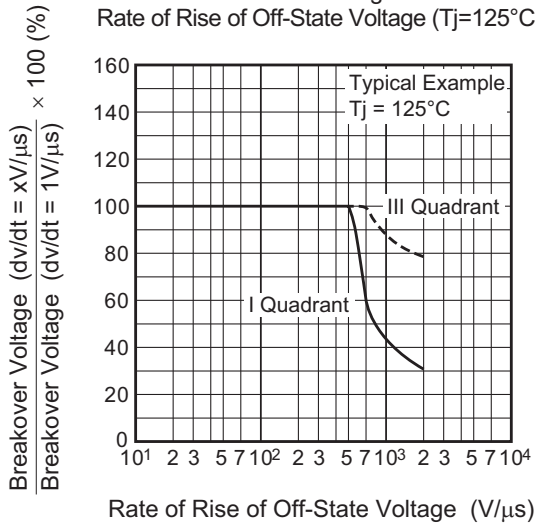
Latching Current vs. Junction Temperature



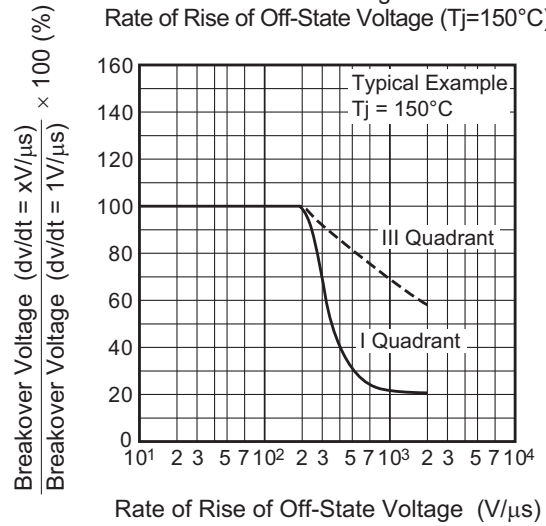
Breakover Voltage vs. Junction Temperature



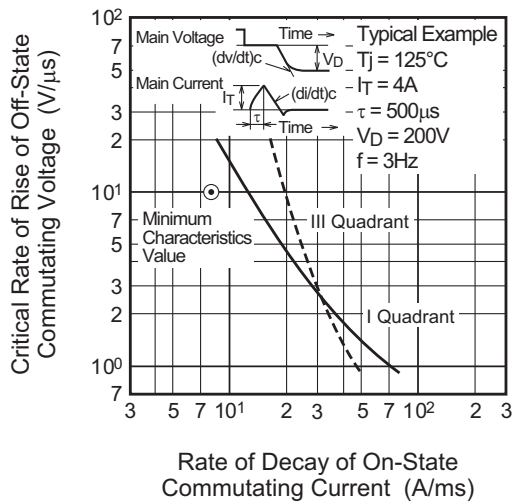
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=125°C)



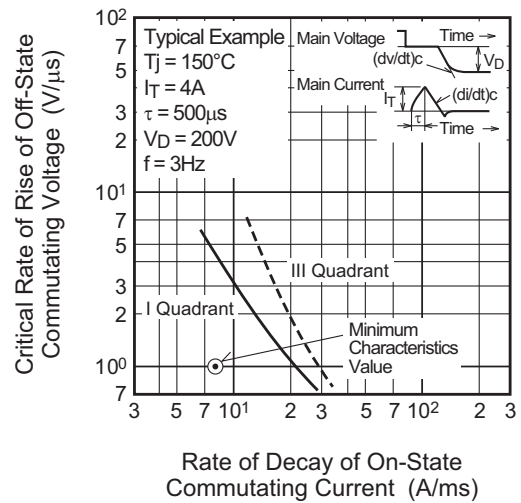
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=150°C)



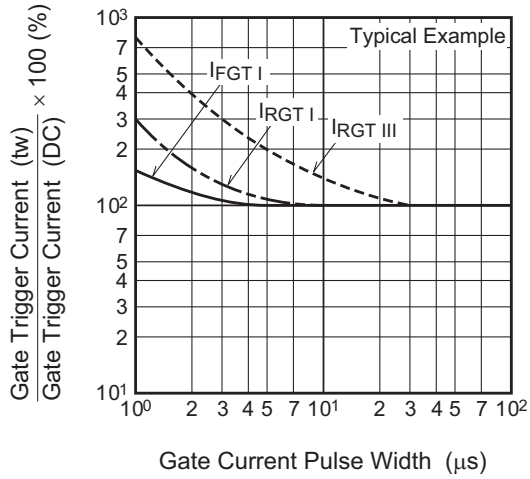
Commutation Characteristics (Tj=125°C)



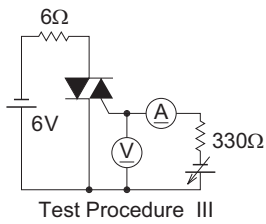
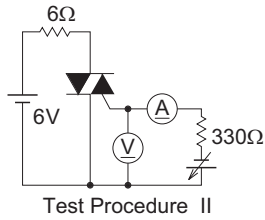
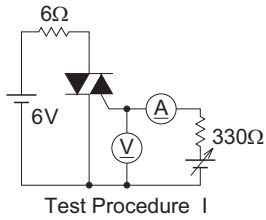
Commutation Characteristics (Tj=150°C)



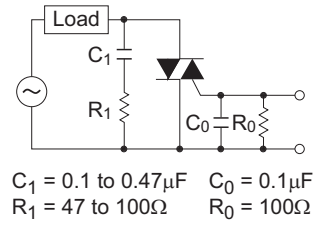
Gate Trigger Current vs. Gate Current Pulse Width



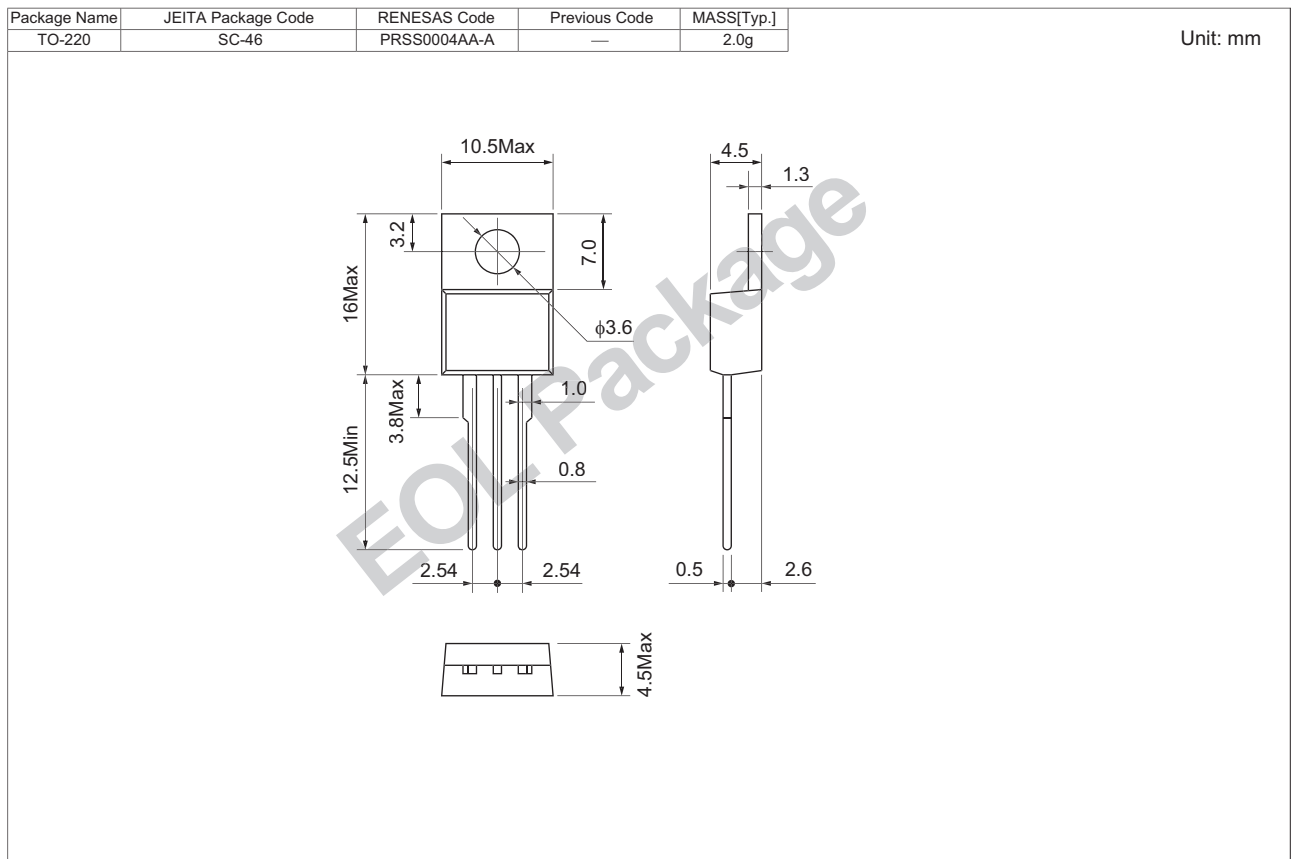
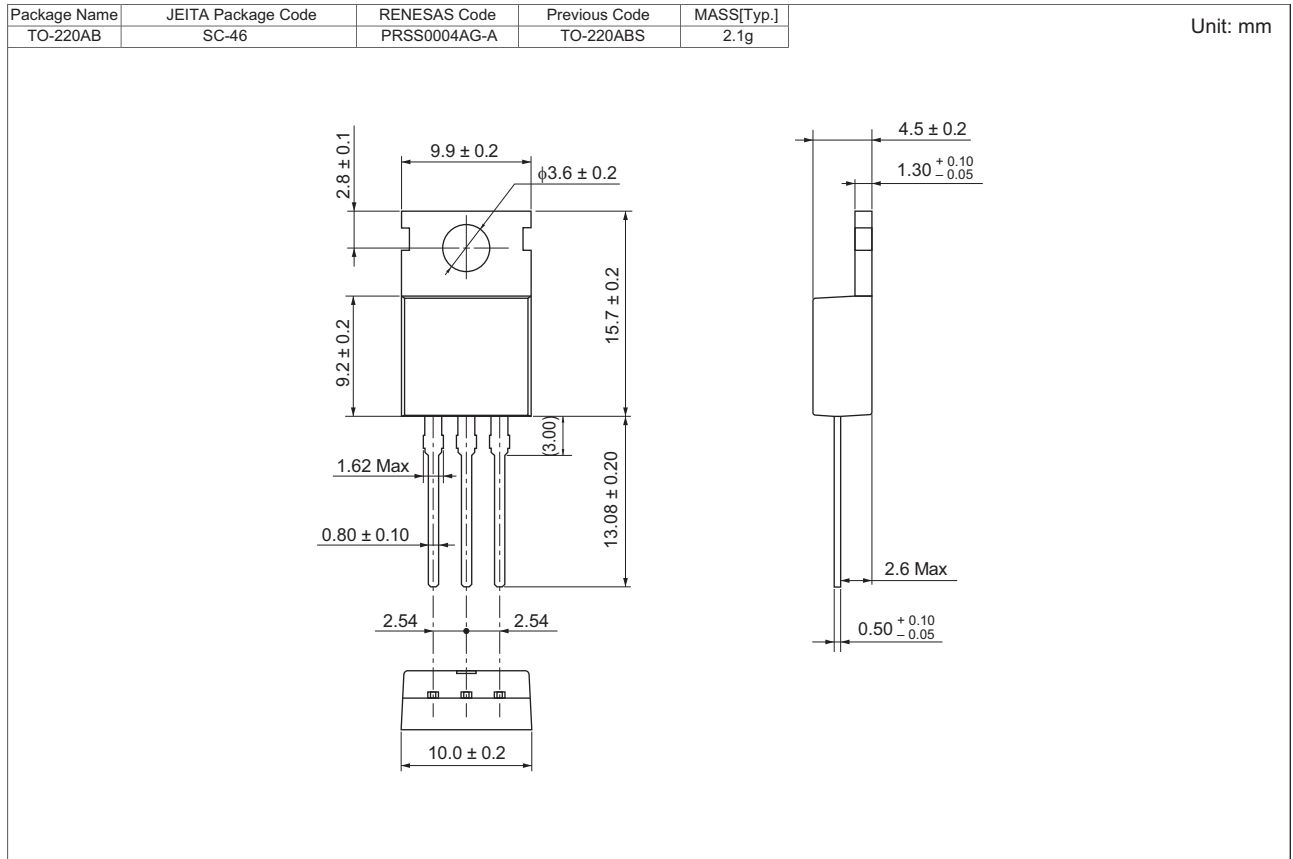
Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac



Package Dimensions



Ordering Information

Orderable Part Number	Packing	Quantity	Remark
BCR16CM-12LB#BB0	Tube	50 pcs.	Straight type
BCR16CM-12LBA8#BB0	Tube	50 pcs.	A8 Lead form

Note: Please confirm the specification about the shipping in detail.

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